



- Low forward voltage and leakage current
- Low inductance package
- High surge current capability

V_{RRM}	2000	V
$I_D(@ T_C = 100^\circ\text{C})$	75	A
$I_{FSM}(@ t_p = 10\text{ms})$	750	A
$V_{FM}(\text{Max})$		

- Field supply for DC motors
- Line rectifiers for transistorized AC motor controllers
- Non-controllable rectifiers for AC/DC converter

(@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RRM}	2000	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	2100	V
Average forward current	$T_C = 100^\circ\text{C}$	I_D	75	A
Forward surge current	1/2 cycle, Sine wave, 50Hz $T_{vj} = 25$	I_{FSM}	750	A
I^2t value for fusing		I^2t	2810	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_{vj}	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	



(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Peak forward voltage	$I_F=75\text{A}$, $t_P=380\mu\text{s}$	V_{FM}		1.20	1.40	V
Reverse leakage current	$V_R = V_{RRM}$, $T_{vj} = 25$	I_{RRM}			0.2	mA
	$V_R = V_{RRM}$, $T_{vj} = 150$				3	mA
Threshold voltage	$T_{vj} = 150$, for power loss calculation only	V_{TO}			0.92	V
Dynamic resistance		r_T			4.8	mΩ

(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Thermal resistance, junction to case	per diode	$R_{th(j-c)}$			1.3	K/W
Thermal resistance, case to heatsink	per module	$R_{th(c-s)}$			0.2	K/W
Mounting torque	Module and heatsink fixed torque	M	2.5		3.5	N m

JMD75TD20D0	JMD75TD20D0	D0	78g/PCS	28PCS	140PCS

FIG.1: Forward characteristics(per diode)

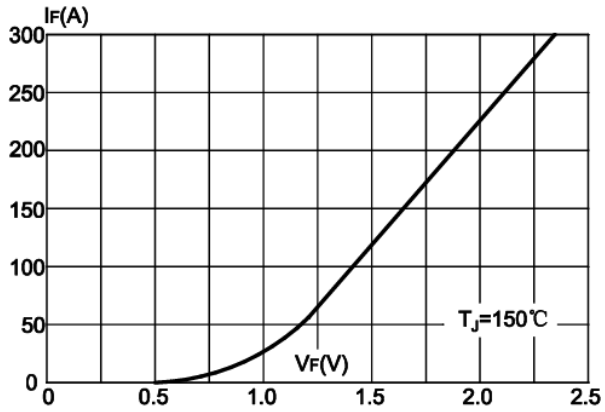


FIG.2: Peak on-state surge current

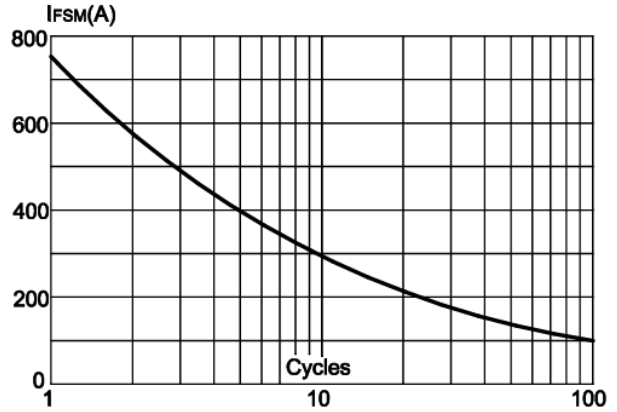
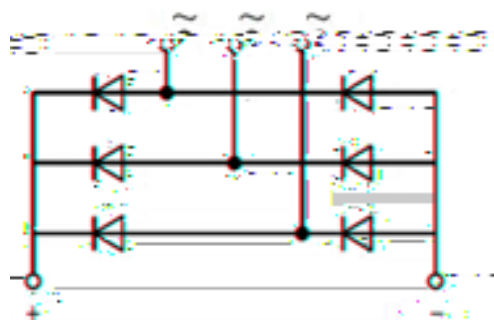
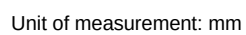


FIG.3: Forward current vs. case temperature



FIG.4: Maximum transient thermal impedance







Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Semiconductor Co., Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. This information in this document is subject to change without prior notice. Notwithstanding this, Jiangsu JieJie will fully comply with the terms outlined in a signed agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document is the initial release, dated 13 August 2026. This document supersedes and replaces all information previously supplied.

 is registered trademark of Jiangsu JieJie Semiconductor Co., Lt ©2026 Jiangsu JieJie Semiconductor Co., Ltd. All rights reserved.